

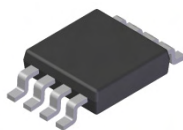
Features

- DIOFET utilizes a unique patented process to monolithically integrate a MOSFET and a Schottky in a single die to deliver:
 - Low $R_{DS(ON)}$ - minimizes conduction losses
 - Low V_{SD} - reducing the losses due to body diode conduction
 - Low Q_{rr} - lower Q_{rr} of the integrated Schottky reduces body diode switching losses
 - Low gate capacitance (Q_g/Q_{gs}) ratio – reduces risk of shoot-through or cross conduction currents at high frequencies
 - Avalanche rugged – I_{AR} and E_{AR} rated
- Lead Free, RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

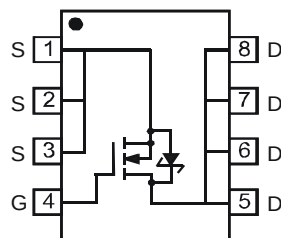
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.072 grams (approximate)

DIOFET



Top View



Top View
Internal Schematic

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 3) $V_{GS} = 10\text{V}$	Steady State	$T_A = 25^\circ\text{C}$ $T_A = 85^\circ\text{C}$	I_D	11 6.6	A
Pulsed Drain Current (Note 4)			I_{DM}	80	A
Avalanche Current (Notes 4 & 5)			I_{AR}	17	A
Repetitive Avalanche Energy (Notes 4 & 5) $L = 0.3\text{mH}$			E_{AR}	43	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P_D	1.55	W
Thermal Resistance, Junction to Ambient @ $T_A = 25^\circ\text{C}$ (Note 3)	$R_{\theta JA}$	81.3	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
- No purposefully added lead.
 - Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 - Device mounted on 1in * 1in FR-4 PCB with 2oz. Copper. The value in any given application depends on the user's specific board design.
 - Repetitive rating, pulse width limited by junction temperature.
 - I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep $T_J = 25^\circ\text{C}$

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	-	-	0.1	mA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	1.0	1.5	2.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	8.5	11.9	mΩ	V _{GS} = 10V, I _D = 11A
			9.5	14.9		V _{GS} = 4.5V, I _D = 8.8A
Forward Transfer Admittance	Y _{fs}	-	18	-	S	V _{DS} = 5V, I _D = 10A
Diode Forward Voltage	V _{SD}	-	0.45	0.55	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	-	1276	-	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	160	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	136	-	pF	
Gate Resistance	R _g	0.3	1.48	2.7	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	-	14.3	-	nC	V _{DS} = 15V, V _{GS} = 4.5V, I _D = 8.8A
Total Gate Charge (V _{GS} = 10V)	Q _g	-	30.6	-	nC	
Gate-Source Charge	Q _{gs}	-	3.4	-	nC	V _{DS} = 15V, V _{GS} = 10V, I _D = 8.8A
Gate-Drain Charge	Q _{gd}	-	4.3	-	nC	
Turn-On Delay Time	t _{D(on)}	-	15.8	-	ns	V _{GS} = 4.5V, V _{DS} = 15V, R _G = 1.8Ω, I _D = 8.8A
Turn-On Rise Time	t _r	-	27.8	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	29.7	-	ns	
Turn-Off Fall Time	t _f	-	13.6	-	ns	

Notes: 6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to production testing.

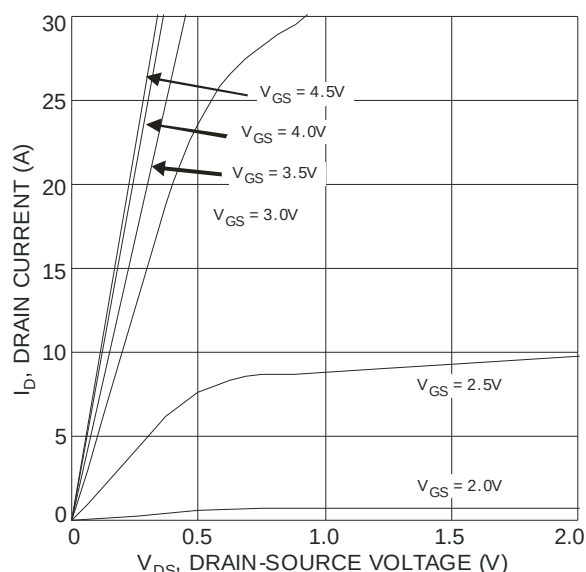


Fig. 1 Typical Output Characteristics

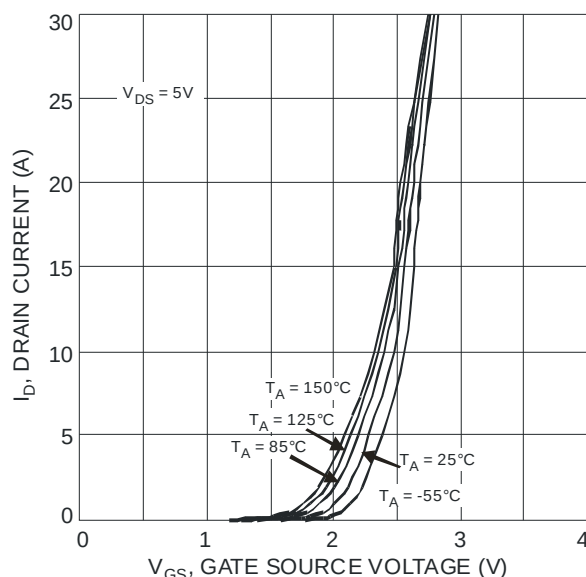
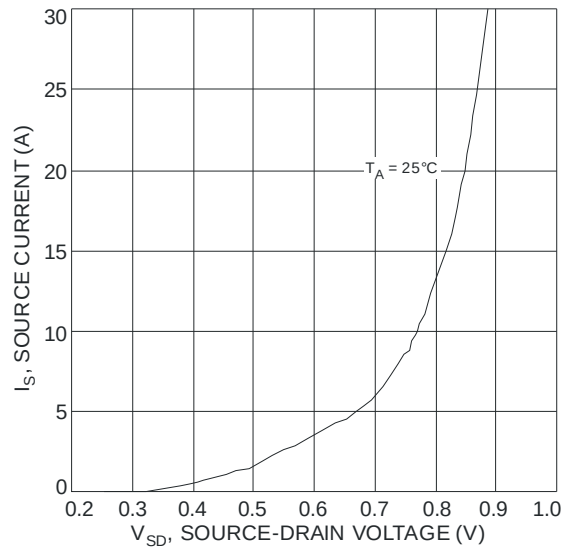
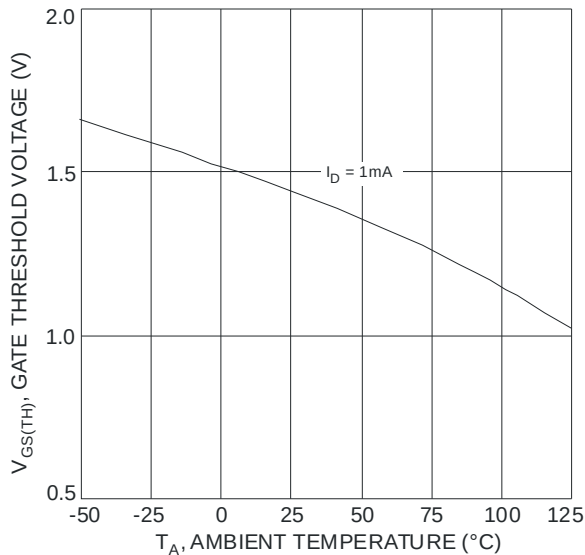
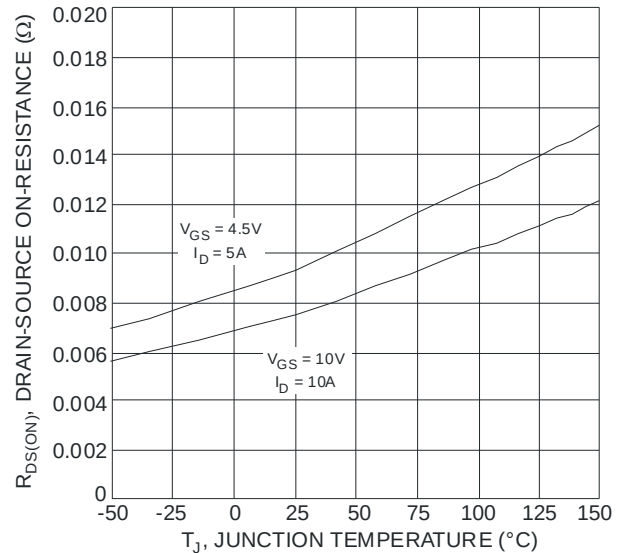
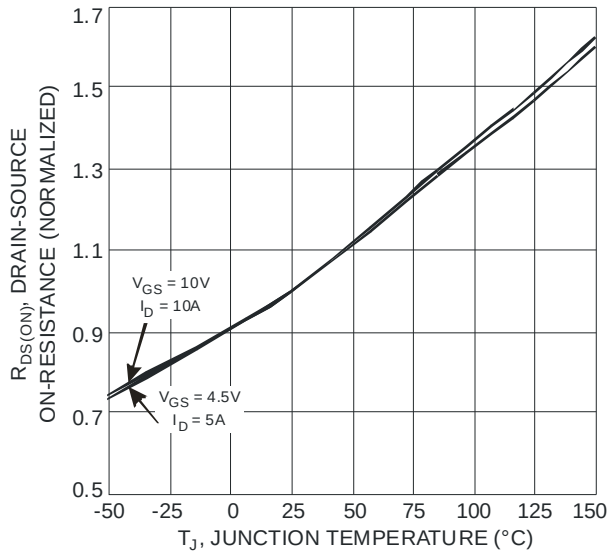
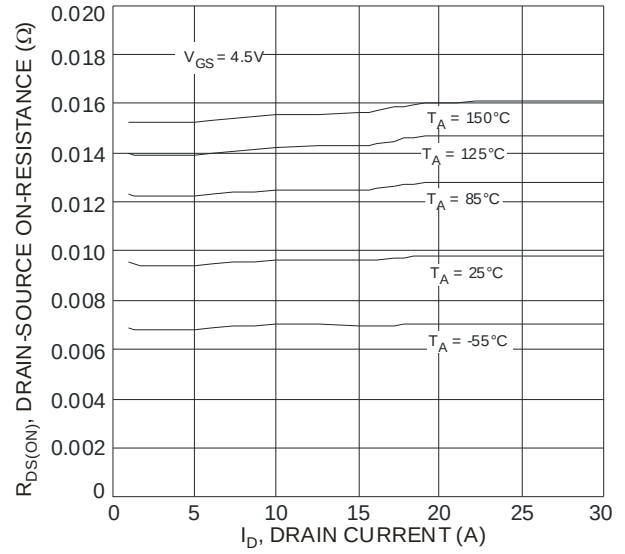
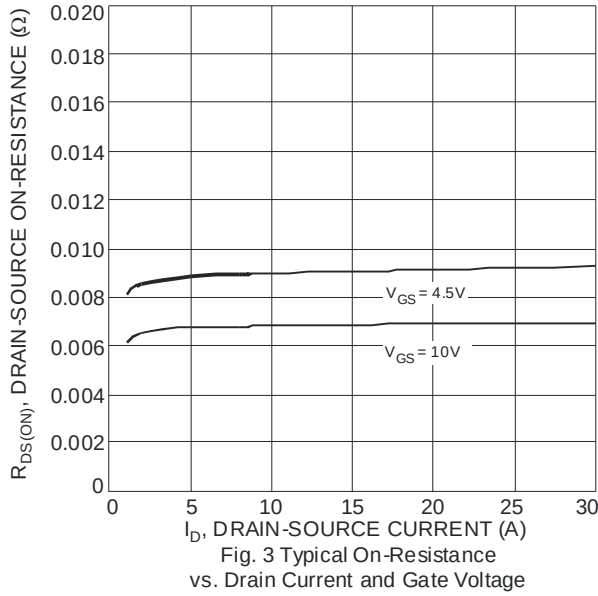
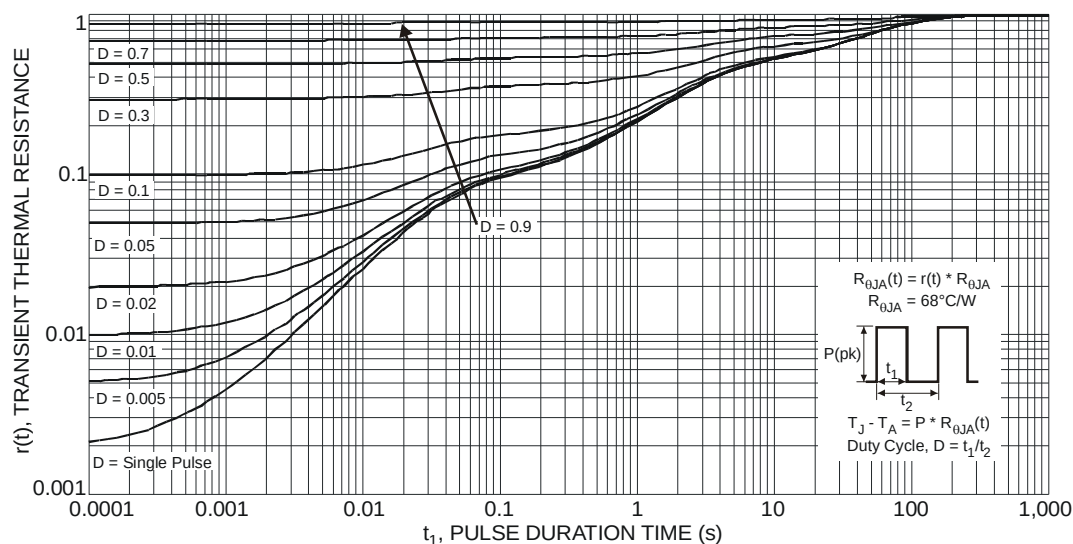
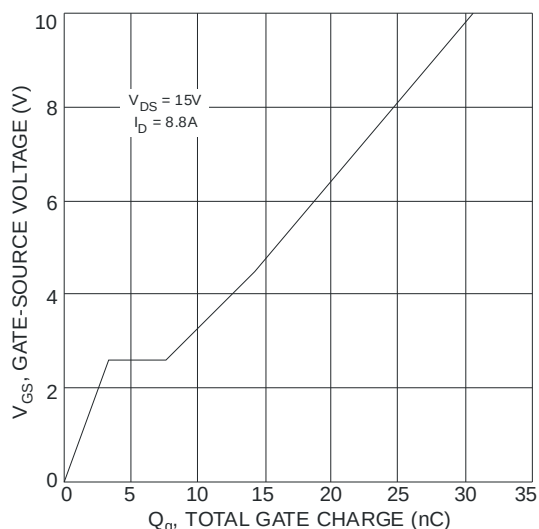
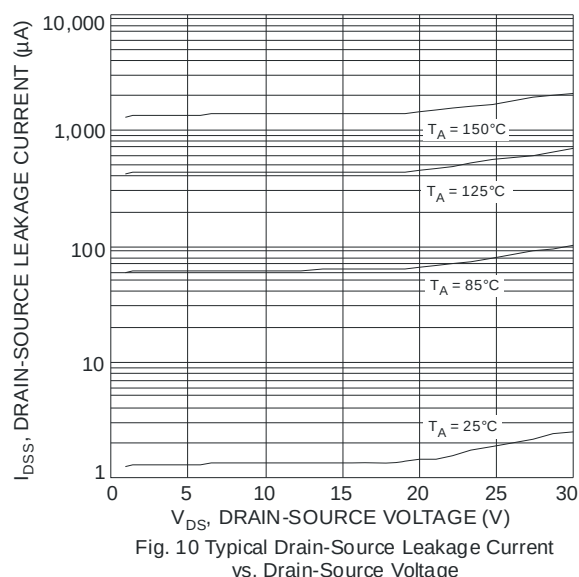
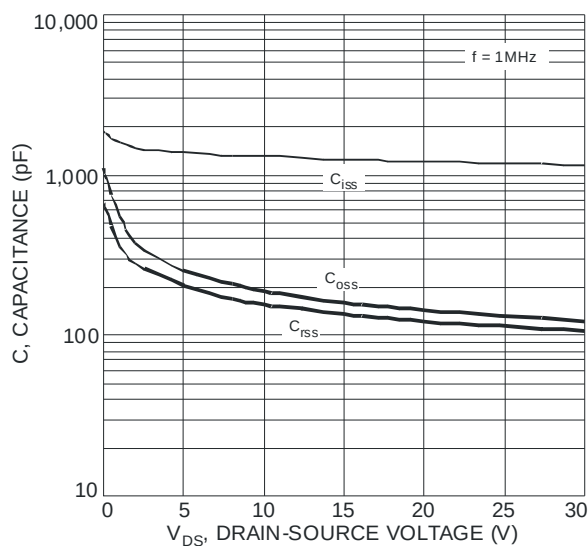


Fig. 2 Typical Transfer Characteristics



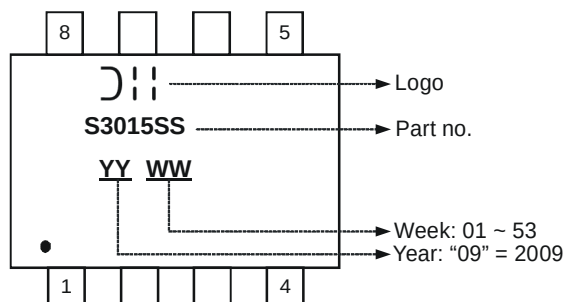


Ordering Information (Note 8)

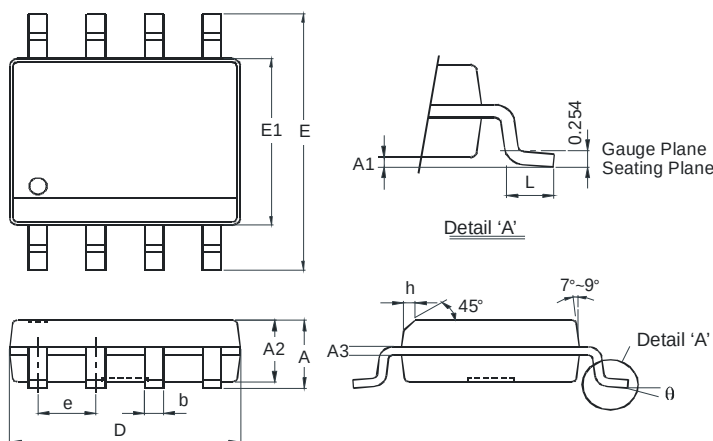
Part Number	Case	Packaging
DMS3015SSS-13	SO-8	2500 / Tape & Reel

Notes: 8. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information

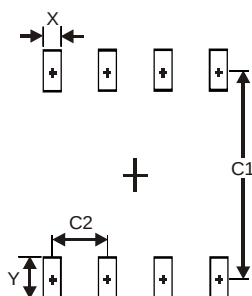


Package Outline Dimensions



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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